

WET BENCH: OXIDE ETCH + HYDROPHILIC CLEAN (RCA CLEAN)

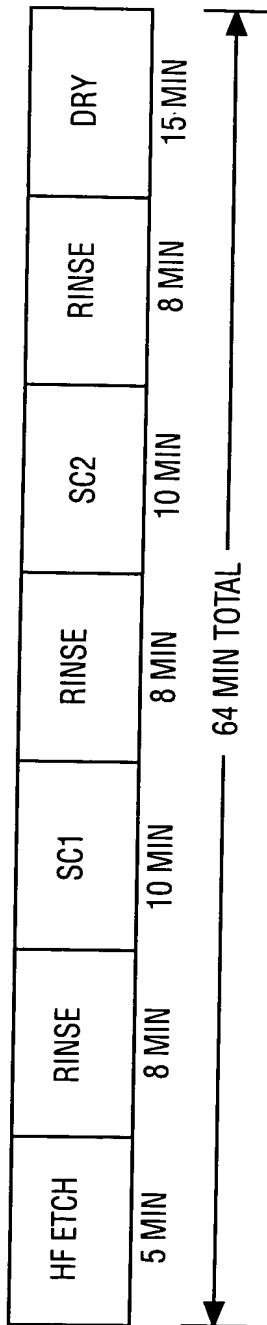


FIG. 1a

SINGLE WAFER CLEANING TOOL SINGLE STEP CLEAN  
OXIDE ETCH + HYDROPHILIC CLEAN

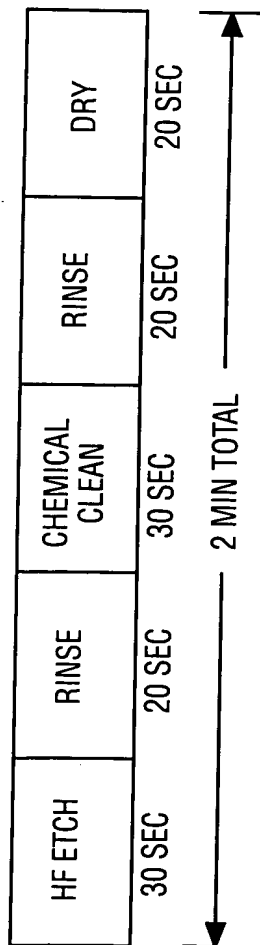


FIG. 1b

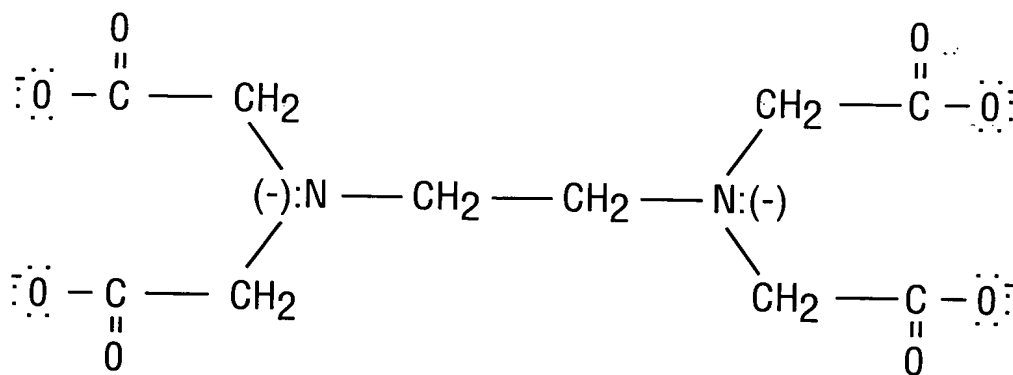


FIG. 2a

$\downarrow$   
 BINDS METAL IONS

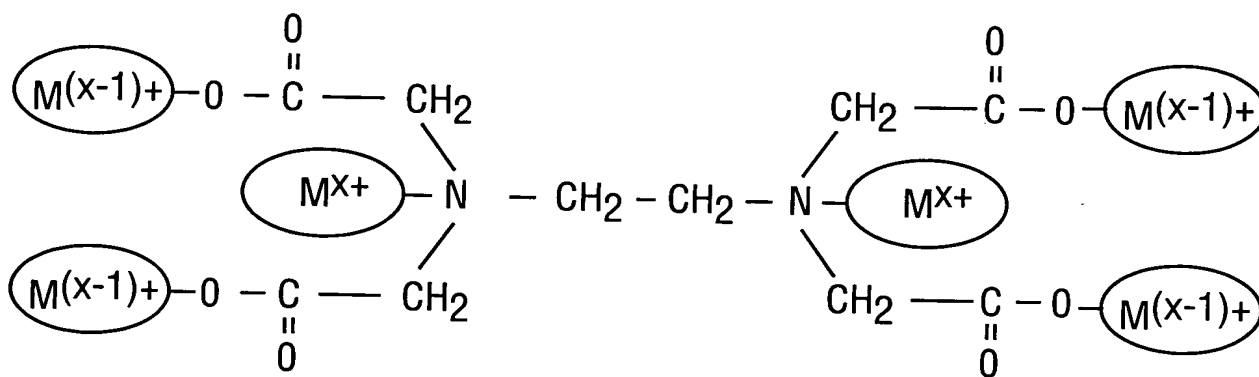
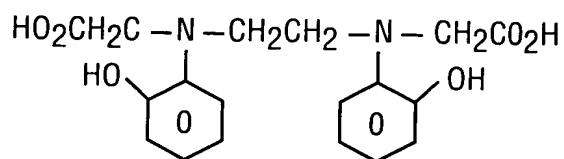
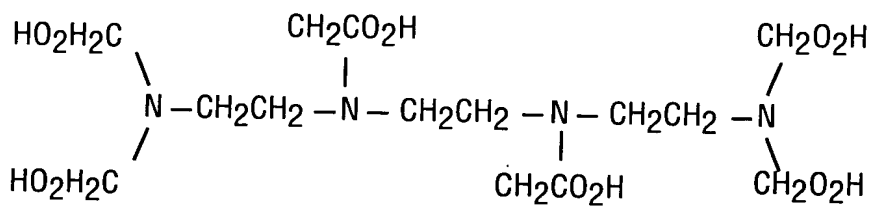


FIG. 2b



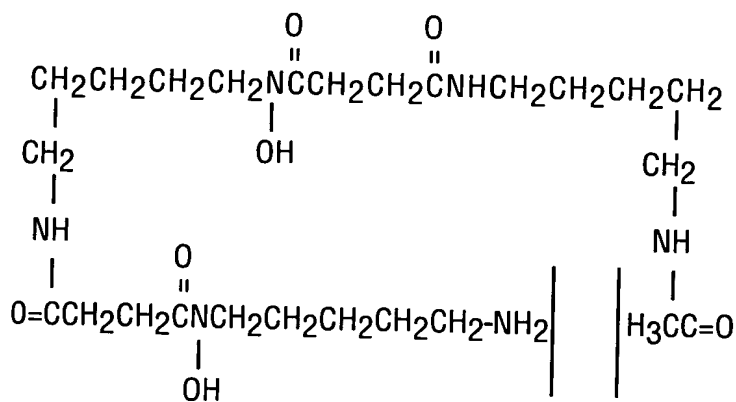
(HPED)

FIG. 3a



(TTHA)

FIG. 3b



DESFERRIFERRIOXAMIN B

FIG. 3c

O=C(N)CCC(=O)N[C@@H]1C[C@H](C)[C@H](C)[C@@H](CNC(=O)CCC(=O)O)C1

FIG. 3d

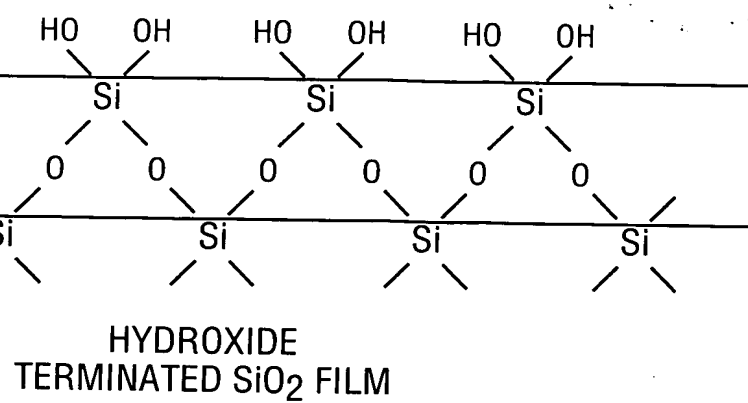


FIG. 4a

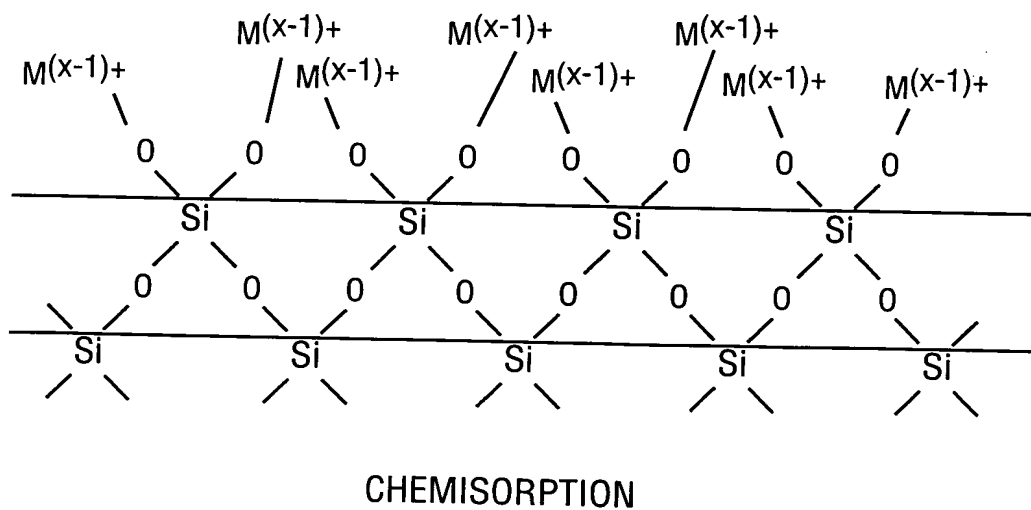


FIG. 4b

The diagram illustrates a particle and a silicon surface. The upper part shows a central oval labeled "PARTICLE" with five wavy lines extending from it to five separate ovals, each labeled  $\text{SO}_4^-$ . A dimension line with the number "500" is positioned near the top right of the particle. The lower part shows a horizontal line representing the "SILICON SURFACE 510". Four wavy lines extend from this surface to four separate ovals, each labeled  $\text{SO}_4^-$ .

FIG. 5

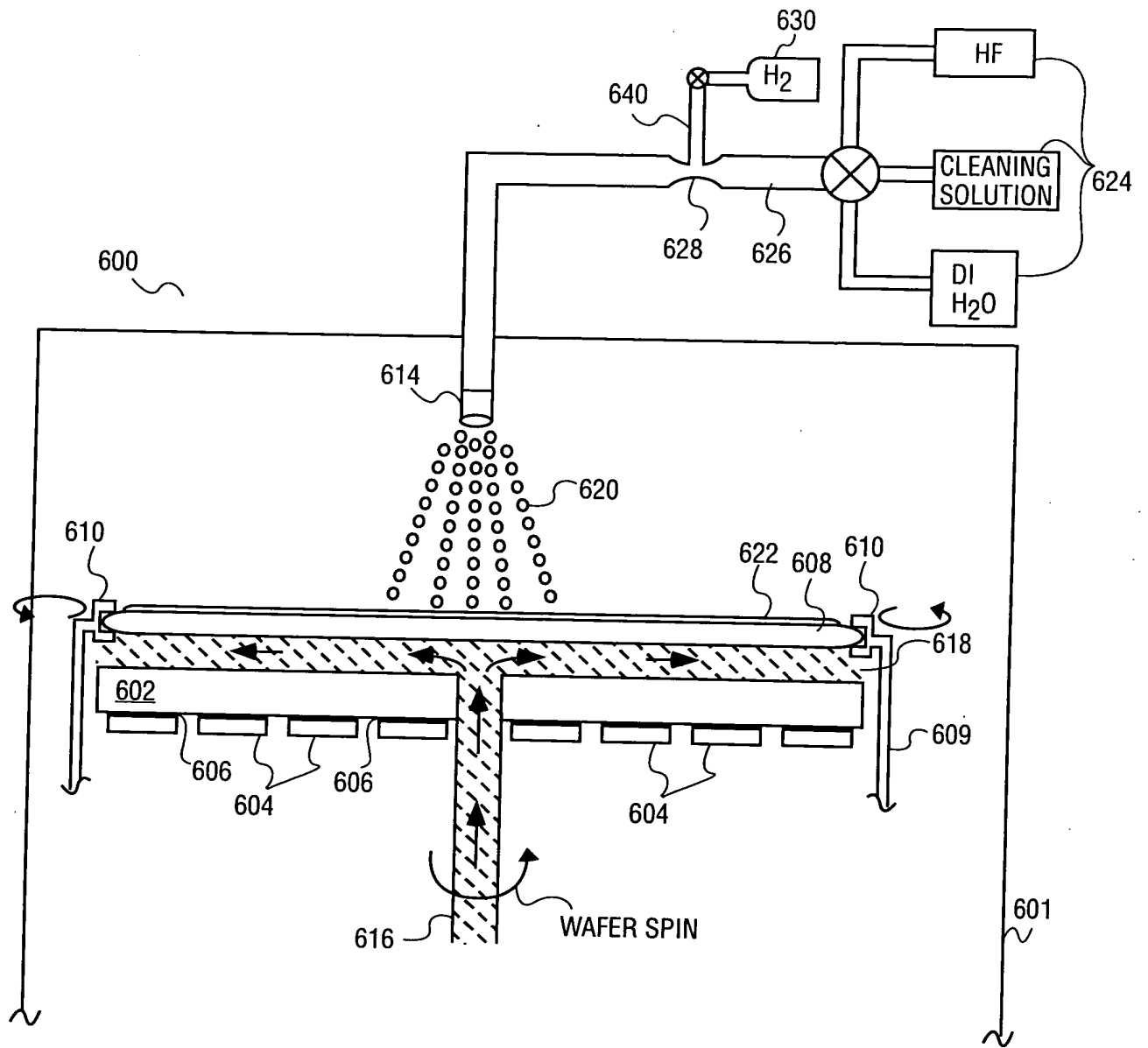


FIG. 6a

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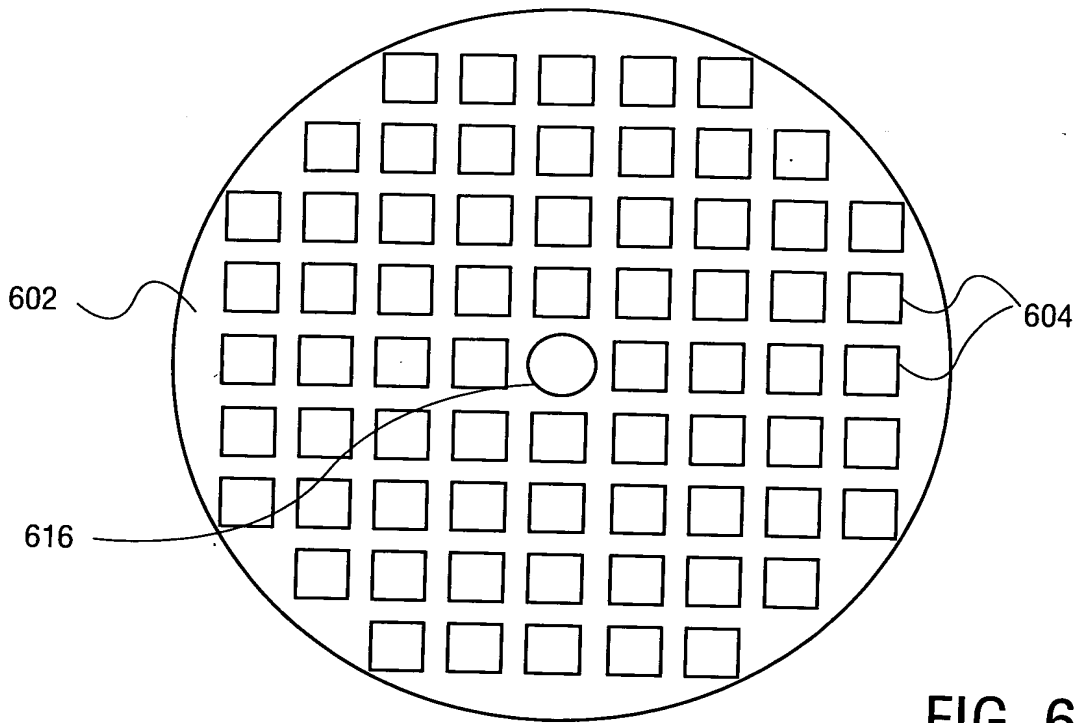


FIG. 6b

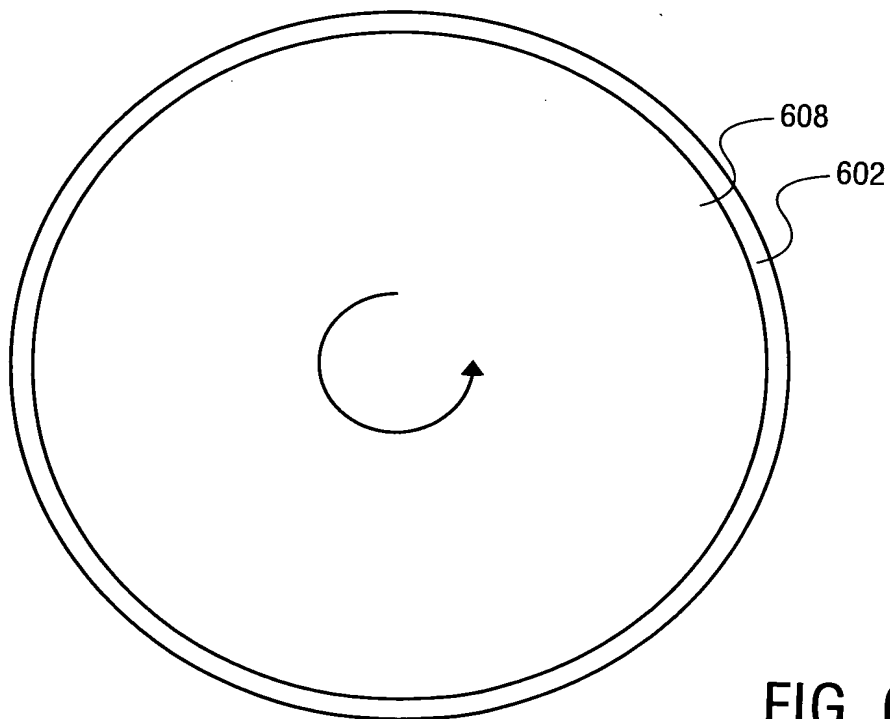


FIG. 6c



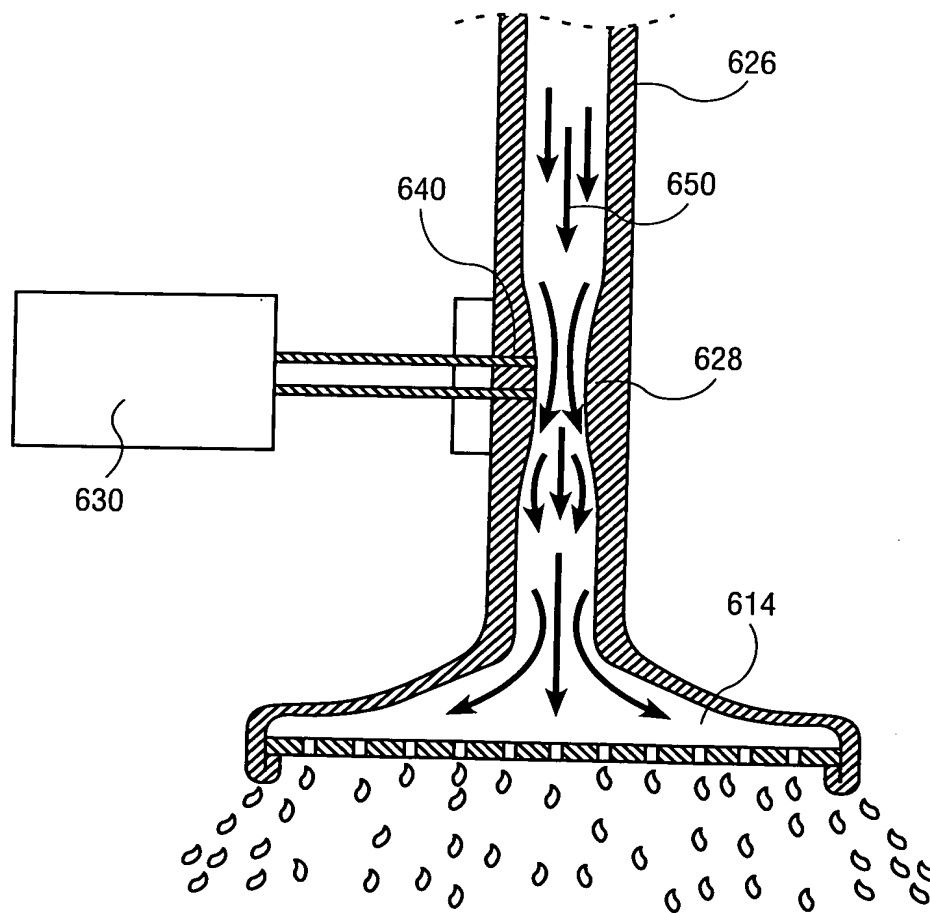


FIG. 6d

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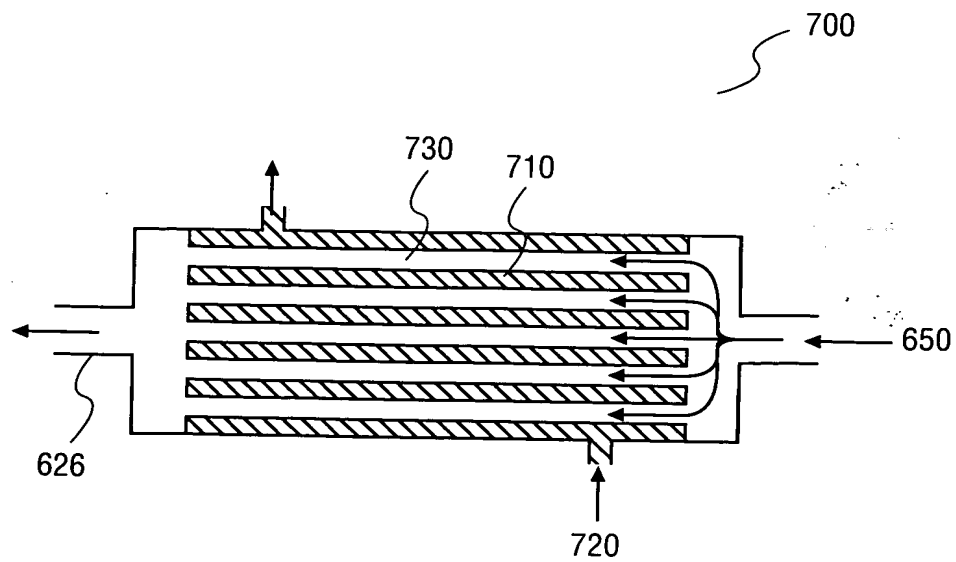


FIG. 7a

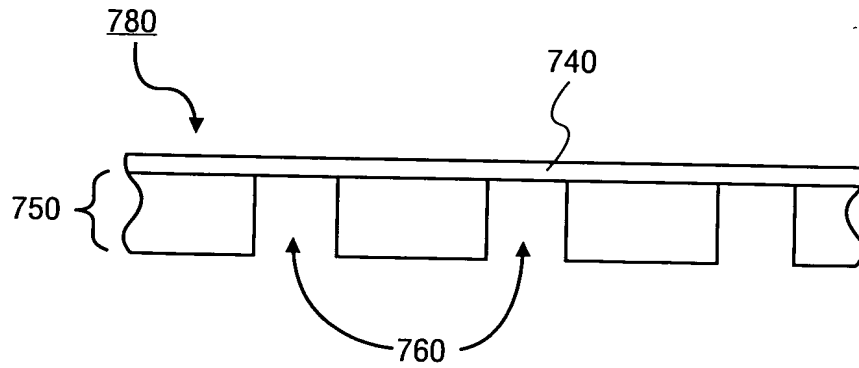


FIG. 7b

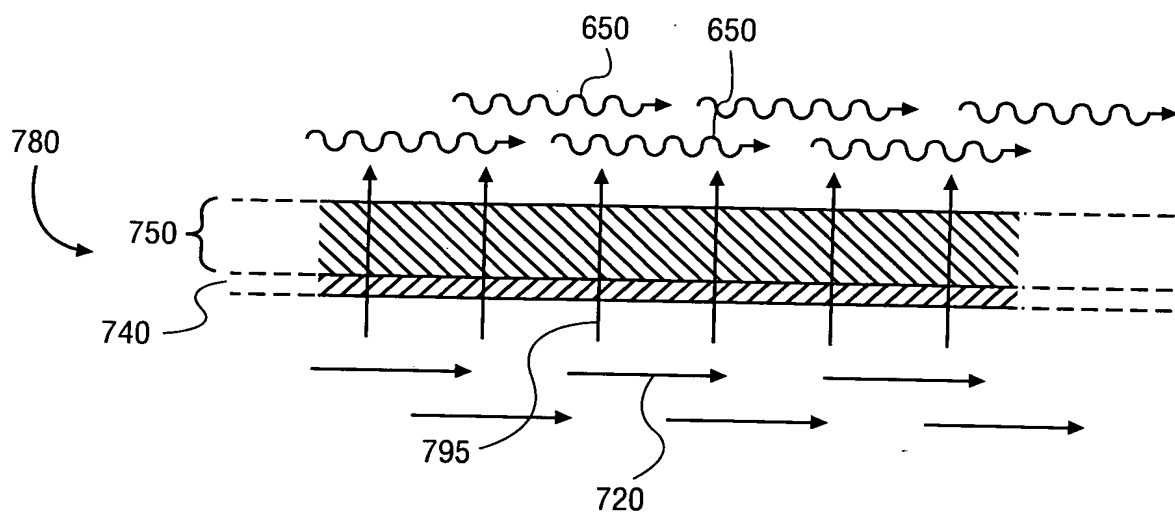


FIG. 7c

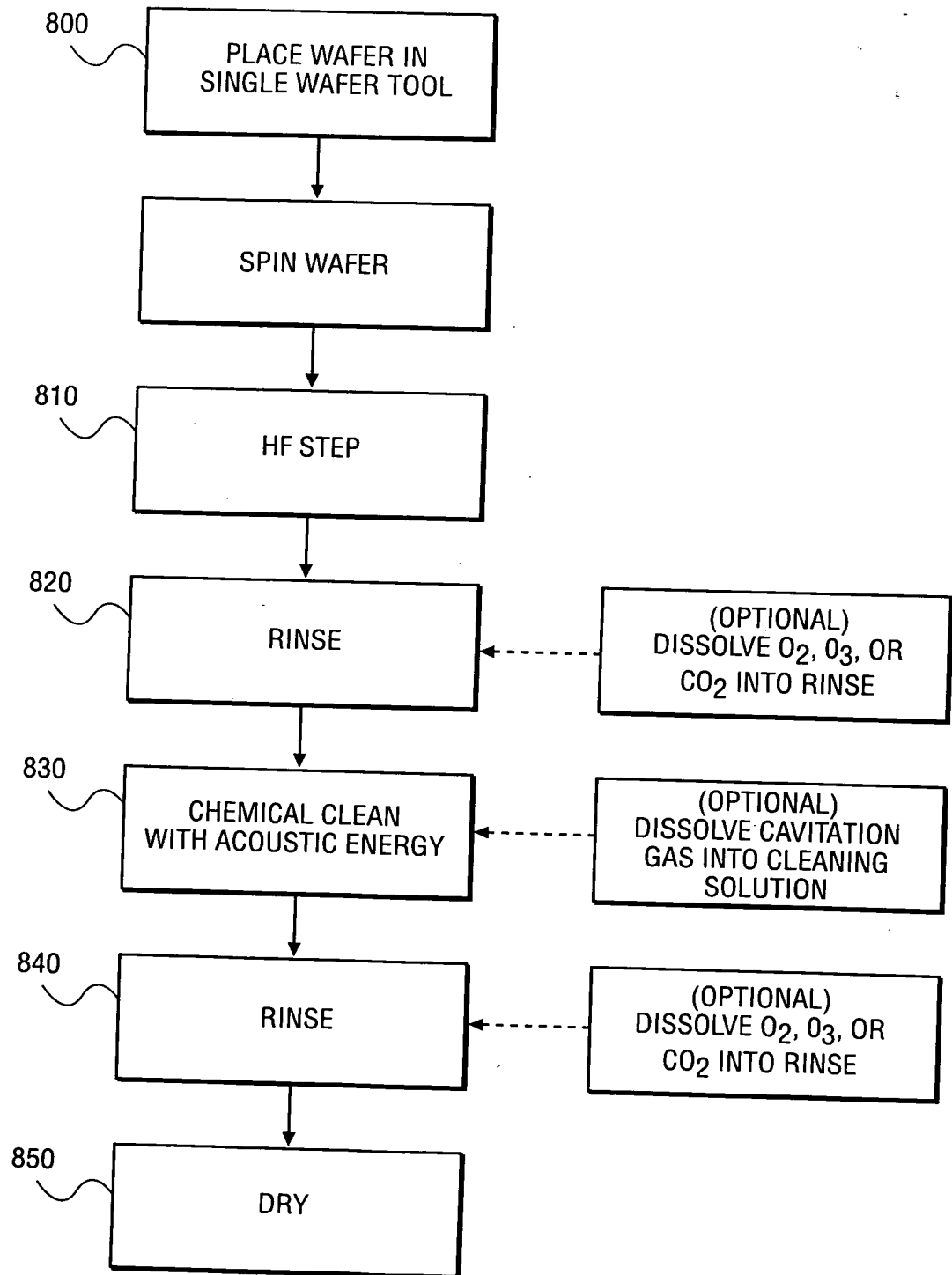


FIG. 8

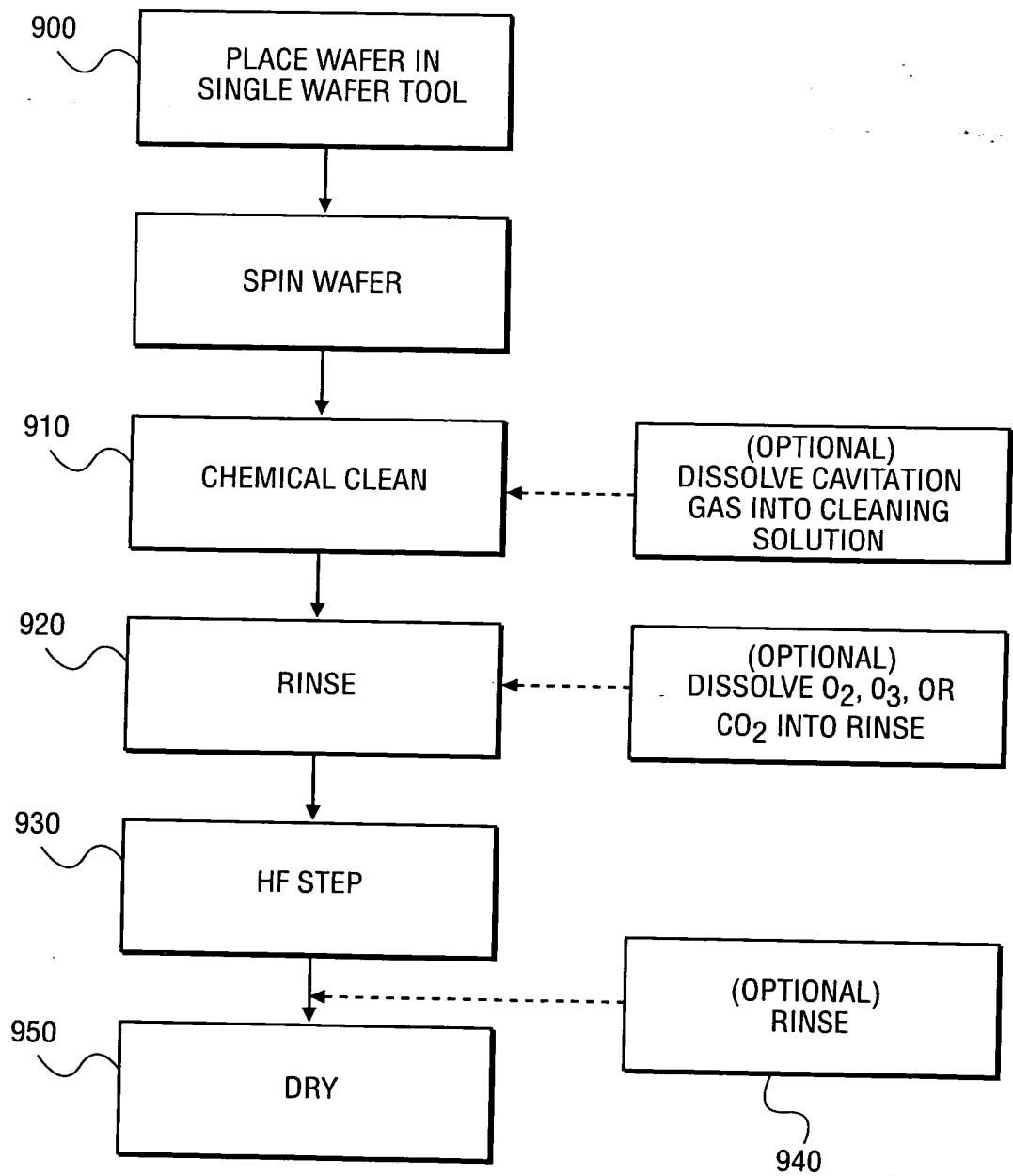


FIG. 9

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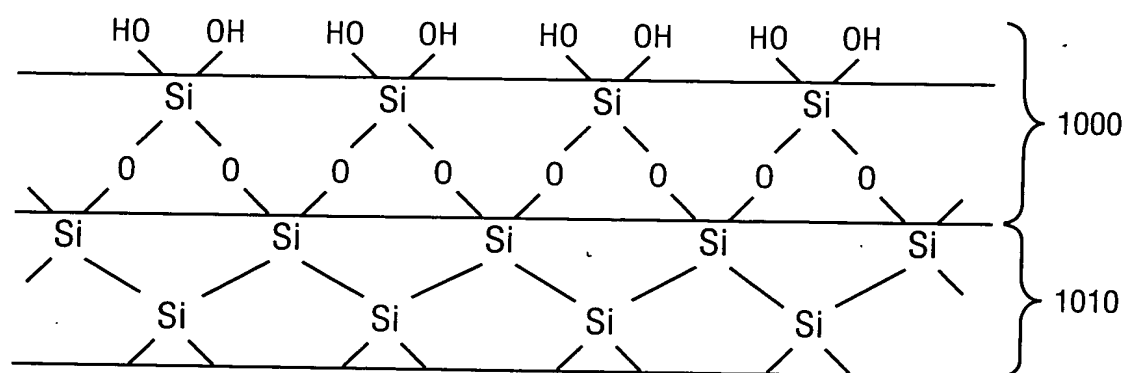
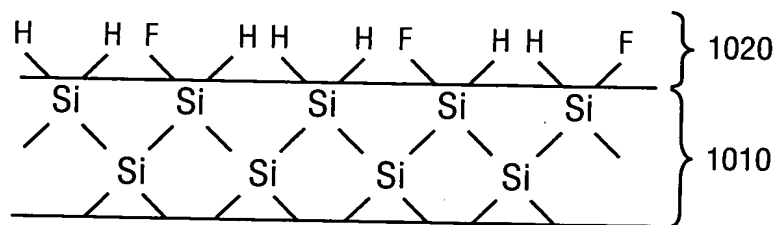


FIG. 10a



HYDROPHOLIC SURFACE

FIG. 10b

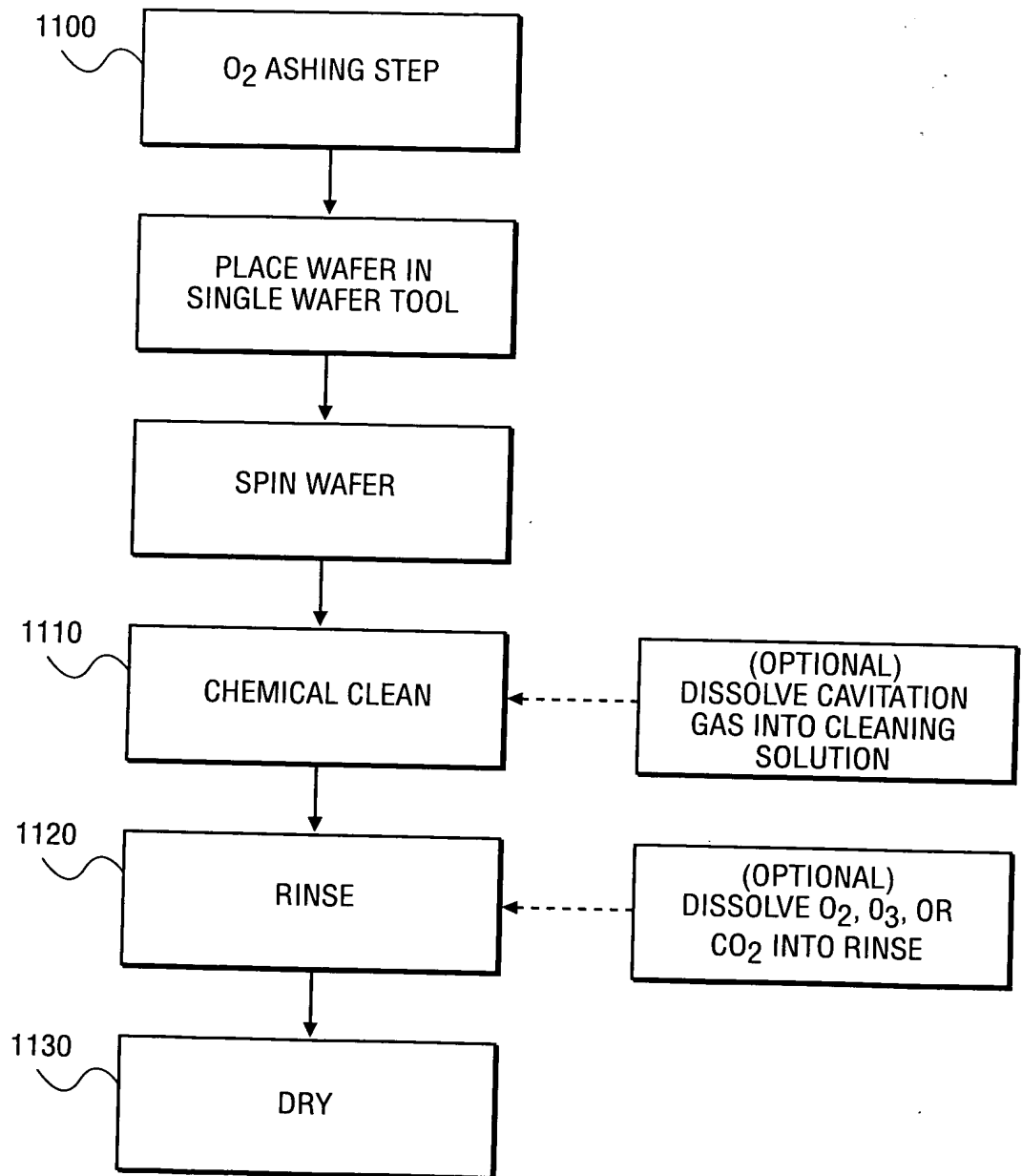


FIG. 11

2007-09-04 09:00

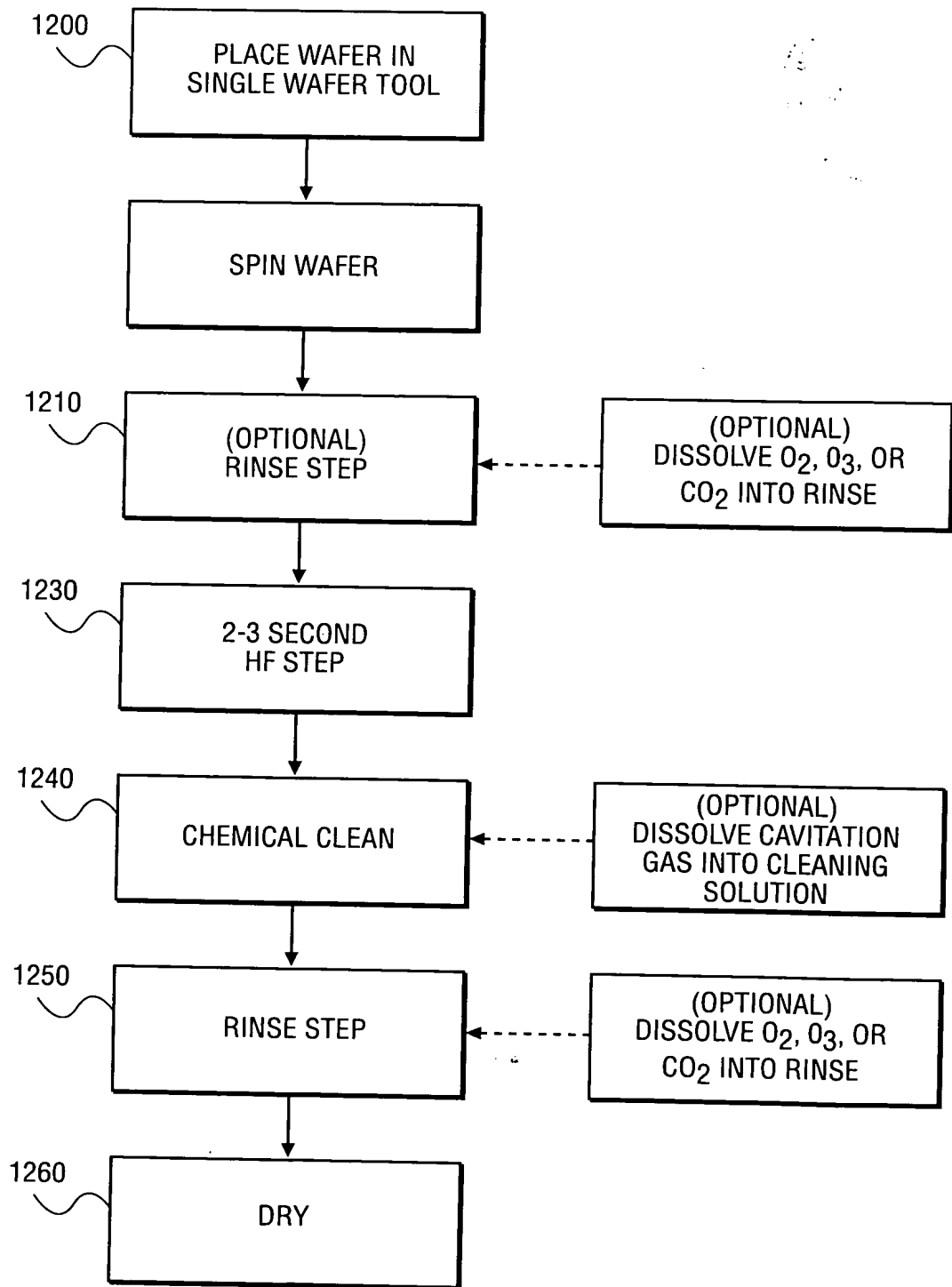


FIG. 12



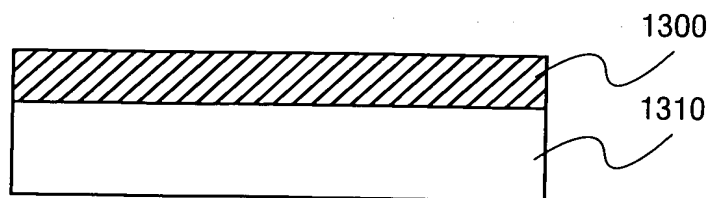


FIG. 13a

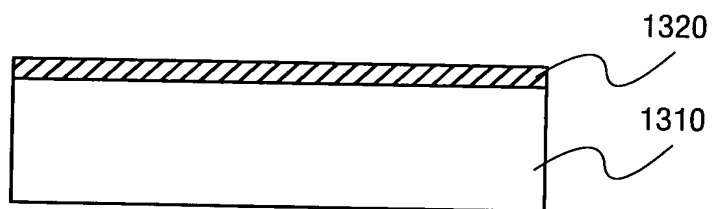


FIG. 13b

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